

T2500D





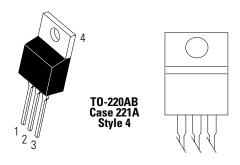
Description

Designed primarily for full-wave ac control applications, such as light dimmers, motor controls, heating controls and power supplies.

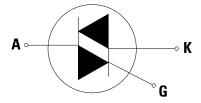
Features

- Blocking Voltage 400 V
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- High Surge Current Capability 60 A Peak at T_C
 = 80°C
- Pb–Free Package is Available

Pin Out



Functional Diagram



Additional Information







Resources



Samples



Maximum Ratings (T₁ = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (Sine Wave 50 to 60 Hz, T_J = -40 to +100°C, Gate Open)	V _{DRM} , V _{RRM}	400	V
On-State RMS Current (Full Cycle Sine Wave 50 to 60 Hz) ($T_{\rm C} = +80$ °C)	I _{T (RMS)}	6.0	А
Peak Non-Repetitive Surge Current (One Full Cycle, Sine Wave 60 Hz, T _C = +80°C)	I _{TSM}	60	А
Circuit Fusing Considerations (t = 8.3 ms)	l²t	15	A2s
Peak Gate Power (Pulse Width = 10 μ sec, $T_c = +80$ °C)	P _{GM}	16	W
Average Gate Power (t = 8.3 msec, $T_c = +80^{\circ}$ C)	P _{GM (AV)}	0.2	W
Peak Gate Current (Pulse Width = 10 µsec)	I _{GM}	4.0	А
Operating Junction Temperature Range @ Rated V _{RRM} and V _{DRM}	T _J	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

Thermal Characteristics

Rating	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R _{BJC}	2.7	°C/W
Maximum Device Temperature for Soldering Purposes for 10 Sec	T _L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Electrical Characteristics - **OFF** (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
†Peak Repetitive Blocking Current	T, = 25°C	I _{DRM} ,	-	-	10	μА
$(V_{AK} = V_{DRM} = V_{RRM}; Gate Open)$	$T_J = 100^{\circ}C$	I _{RRM}	-	-	2.0	mA

Electrical Characteristics - ON (T_c = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Forward On-State Voltage (Note 3) (I _{TM} = ±30 A)		V _{TM}	_	-	2.0	V
	MT2(+), G(+)		_	10	25	
Gate Trigger Current (Continuous dc)	MT2(+), G(-)		_	20	60	A
$(V_{D} = 12 \text{ V}, R_{L} = 100 \Omega)$	MT2(-), G(-)	GT	_	15	25	- mA
	MT2(-), G(+)		_	30	60	
Gate Trigger Voltage (Continuous dc) (All Four Quadrants) $(V_p = 12 \text{ Vdc}, R_1 = 100 \Omega)$		V _{GT}	_	1.25	2.5	V
Gate Non-Trigger Voltage (Continuous dc) $(V_p = 12 \text{ Vdc}, R_1 = 100 \Omega, T_c = 100^{\circ}\text{C})$		V _{GD}	0.2	-	_	V
Holding Current (Main Terminal Voltage = 12 Vdc, Gate Open , Initiating Current) = ± 200 mA)		I _H	_	15	30	mA
Gate Controlled Turn-On Time (Rated V_{DRM} , $I_T=10$ A , $I_{GT}=160$ mA, Rise Time = 0.1 μ s)		t _{gt}	_	1.6	_	μs

Dynamic Characteristics

Characteristic	Symbol	Min	Тур	Max	Unit
Critical Rate of Rise of Off-State Voltage ($V_D = 0.66 \times V_{DBM'}$ Exponential Waveform, Gate Open, $T_J = 100^{\circ}$ C)	dV/dt	_	50	_	V/µs

^{1.} V_{DBM} and V_{BBM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



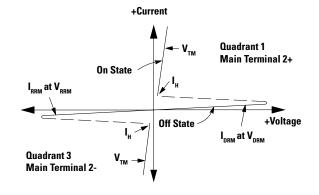
Dynamic Characteristics

Characteristic	Symbol	Min	Тур	Max	Unit
Critical Rate-of-Rise of Commutation Voltage $(V_D = Rated\ V_{DRM'}\ I_{TRMS}) = 6\ A$, Commutating di/dt = 3.2 A/ms, Gate Unenergized, $T_C = 80^{\circ}\text{C}$)	dv/dt	-	10	_	V/µs
Critical Rate-of-Rise of Off-State Voltage (V_D = Rated $V_{DRM'}$ Exponential Voltage Rise, Gate Open, T_C = 100°C)	di/dt	-	75	-	A/µs

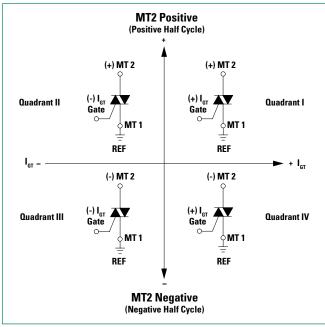
^{2.} Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.

Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Maximum On State Voltage
- I	Holding Current



Quadrant Definitions for a Triac

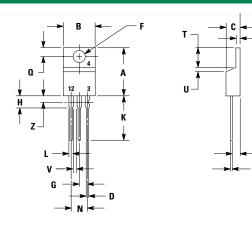


All Polarities are referenced to MT1.

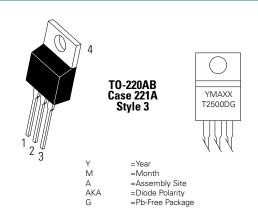
With in-phase signals (using standard AC lines) quadrants I and III are used



Dimensions



Part Marking System



Dim	Inc	hes	Millin	neters
Dim	Min	Max	Min	Max
Α	0.590	0.620	14.99	15.75
В	0.380	0.420	9.65	10.67
С	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.41	2.67
Н	0.110	0.130	2.79	3.30
J	0.018	0.024	0.46	0.61
K	0.540	0.575	13.72	14.61
L	0.060	0.075	1.52	1.91
N	0.195	0.205	4.95	5.21
Q	0.105	0.115	2.67	2.92
R	0.085	0.095	2.16	2.41
S	0.045	0.060	1.14	1.52
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	-	1.15	
Z	_	0.080		2.04

Pin Assignment			
1	Cathode		
2	Anode		
3	Gate		
4	Anode		

Ordering Information

Device	Package	Shipping
T2500D	TO220AB	
T2500DG	TO220AB (Pb-Free)	500 Units/Box

DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
CONTROLLING DIMENSION: INCH.
DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

单击下面可查看定价,库存,交付和生命周期等信息

>>Littelfuse(美国力特)